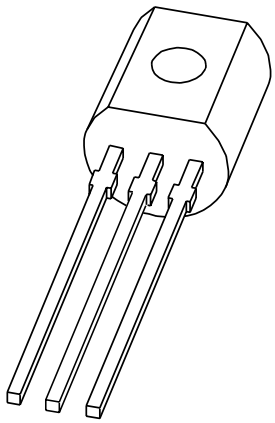
DATA SHEET



PN2907A
PNP switching transistor

Product specification
Supersedes data of 1997 May 05

2004 Oct 11

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PNP switching transistor PN2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a TO-92; SOT54 plastic package. NPN complement: PN2222A.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter

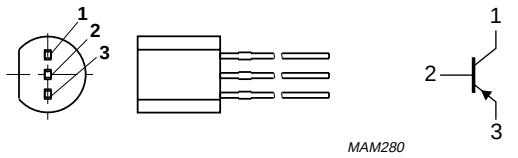


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
I_C	collector current (DC)		–	–600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	500	mW
h_{FE}	DC current gain	V_{CE} = –10 V; I_C = –150 mA	100	300	
f_T	transition frequency	V_{CE} = –20 V; I_C = –50 mA; f = 100 MHz	200	–	MHz
t_{off}	turn-off time	I_{Con} = –150 mA; I_{Bon} = –15 mA; I_{Boff} = 15 mA	–	365	ns

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PN2907A	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

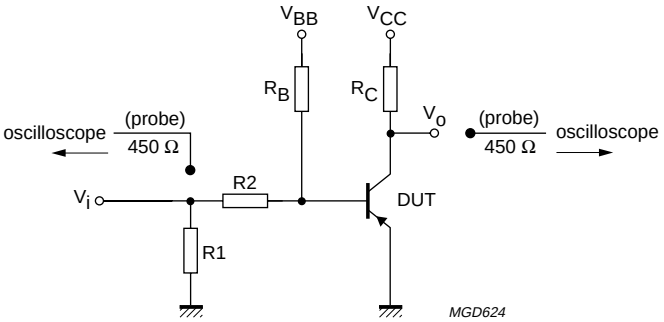
1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –50 V; I_E = 0 A	–	–10	nA
		V_{CB} = –50 V; I_E = 0 A; T_j = 125 °C	–	–10	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0 A	–	–50	nA
h_{FE}	DC current gain	V_{CE} = –10 V; I_C = –0.1 mA	75	–	
		V_{CE} = –10 V; I_C = –1 mA	100	–	
		V_{CE} = –10 V; I_C = –10 mA	100	–	
		V_{CE} = –10 V; I_C = –150 mA	100	300	
		V_{CE} = –10 V; I_C = –500 mA	50	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–400	mV
		I_C = –500 mA; I_B = –50 mA	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–1.3	V
		I_C = –150 mA; I_B = –50 mA	–	–2.6	V
C_c	collector capacitance	V_{CB} = –10 V; $I_E = i_e$ = 0 A; f = 1 MHz	–	8	pF
C_e	emitter capacitance	V_{EB} = –2 V; $I_C = i_c$ = 0 A; f = 1 MHz	–	30	pF
f_T	transition frequency	V_{CE} = –20 V; I_C = –50 mA; f = 100 MHz	200	–	MHz

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Switching times (between 10 % and 90 % levels); see Fig.2					
t_{on}	turn-on time	I_{Con} = –150 mA; I_{Bon} = –15 mA; I_{Boff} = 15 mA	–	40	ns
t_d	delay time		–	12	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	365	ns
t_s	storage time		–	300	ns
t_f	fall time		–	65	ns

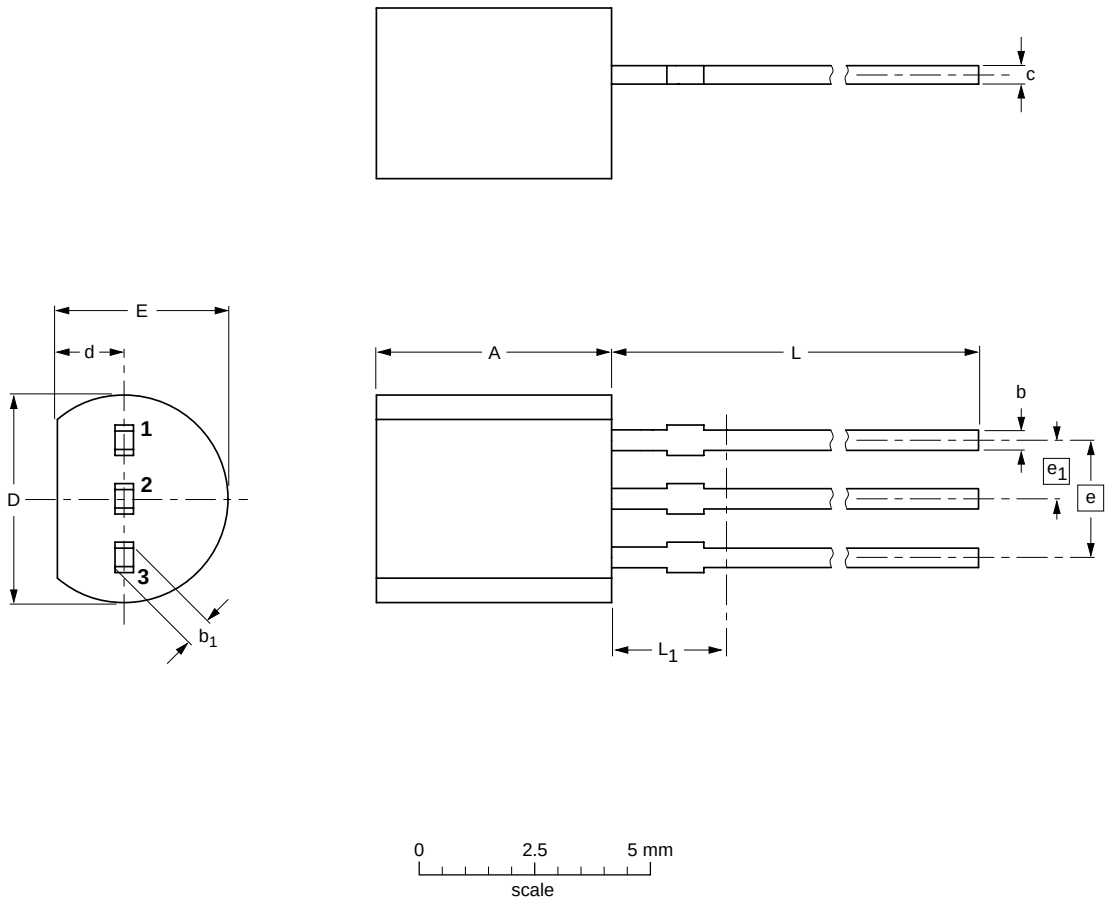


V_i = –9.5 V; T = 500 μs; t_p = 10 μs; t_r = t_f ≤ 3 ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = 3.5 V; V_{CC} = –29.5 V.
Oscilloscope: input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1(1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~97-02-28~~ 04-06-28

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LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
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